

40V DUAL NPN SURFACE MOUNT TRANSISTOR

Features

- V_{CEO} = 40V
- I_C = 200mA
- Epitaxial Planar Die Construction
- Ideally Suited for Automated Assembly Processes
- Lead, Halogen and Antimony Free, RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Ultra Small Package

Mechanical Data

- Case: SOT-963
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper leadframe.
 Solderable per MIL-STD-202, Method 208
- Weight: 0.0027 grams (approximate)

SOT-963



Top View



Device Schematic

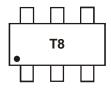
Ordering Information

Device	Packaging	Shipping
DST3904DJ-7	SOT-963	10,000/Tape & Reel

Notes:

- 1. No purposefully added lead. Halogen and Antimony Free.
- 2. Diodes Inc's "Green" Policy can be found on our website at http://www.diodes.com

Marking Information



T8 = Product Type Marking Code





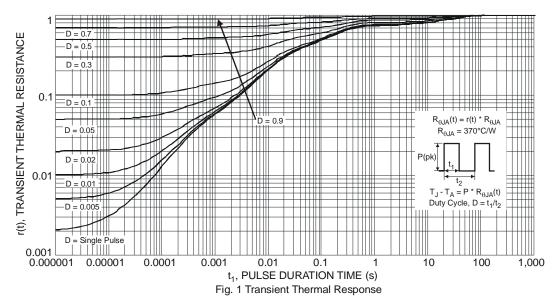
Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Collector Current - Continuous (Note 3)	Ic	200	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3)	P_{D}	300	mW
Thermal Resistance, Junction to Ambient (Note 3)	$R_{ hetaJA}$	417	°C/W
Operating and Storage Temperature Range	T_J , T_{STG}	-55 to +150	°C

Notes: 3. Device mounted on FR-4 PCB with minimum recommended pad layout.



1,000

Single Pulse $R_{\theta,JA}(t) = r(t) * R_{\theta,JA}$ $R_{\theta,JA} = 370 ^{\circ} C/W$ $T_J - T_A = P * R_{\theta,JA}(t)$ Duty Cycle, $D = t_1/t_2$ 0.1

0.00001

0.001

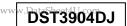
0.1

10

1, PULSE DURATION TIME (s)

Fig. 2 Single Pulse Maximum Power Dissipation

Fig. 3 Power Dissipation vs. Ambient Temperature

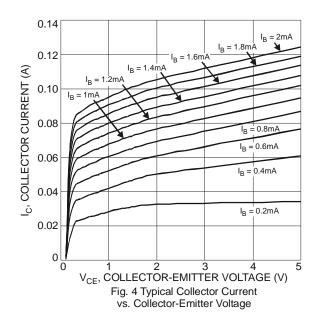


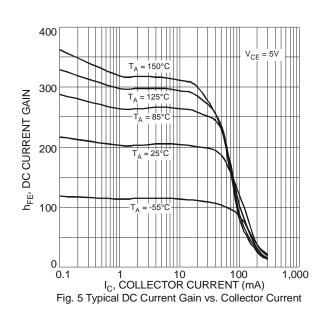


Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition	
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	60	_	V	$I_C = 10\mu A, I_E = 0$	
Collector-Emitter Breakdown Voltage (Note 4)	$V_{(BR)CEO}$	40		V	$I_C = 1.0 \text{mA}, I_B = 0$	
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6.0		V	$I_E = 10\mu A, I_C = 0$	
Collector Cutoff Current	I _{CEX}	_	50	nA	$V_{CE} = 30V, V_{EB(OFF)} = 3.0V$	
Base Cutoff Current	I_{BL}	_	50	nA	$V_{CE} = 30V, V_{EB(OFF)} = 3.0V$	
ON CHARACTERISTICS (Note 4)						
		40	_		$I_C = 100\mu A, V_{CE} = 1.0V$	
		70	_		$I_C = 1.0 \text{mA}, V_{CE} = 1.0 \text{V}$	
DC Current Gain	h _{FE}	100	300	_	$I_C = 10 \text{mA}, V_{CE} = 1.0 \text{V}$	
		60	_		$I_C = 50 \text{mA}, V_{CE} = 1.0 \text{V}$	
		30	30		$I_C = 100 \text{mA}, V_{CE} = 1.0 \text{V}$	
Collector-Emitter Saturation Voltage	\/a=\a\-		0.20	V	$I_C = 10 \text{mA}, I_B = 1.0 \text{mA}$	
Collector-Emilier Saturation Voltage	V _{CE} (SAT)		0.30	V	$I_C = 50 \text{mA}, I_B = 5.0 \text{mA}$	
Base-Emitter Saturation Voltage	V	0.65	0.85	V	$I_C = 10mA, I_B = 1.0mA$	
ŭ .	V _{BE(SAT)}		0.95	V	$I_C = 50 \text{mA}, I_B = 5.0 \text{mA}$	
SMALL SIGNAL CHARACTERISTICS			1	,	,	
Output Capacitance	C _{obo}	_	4.0	pF	$V_{CB} = 5.0V$, $f = 1.0MHz$, $I_E = 0$	
Input Capacitance	C _{ibo}		8.5	pF	$V_{EB} = 0.5V$, $f = 1.0MHz$, $I_{C} = 0$	
Input Impedance	h _{ie}	1.0	10	kΩ		
Voltage Feedback Ratio	h _{re}	0.5	8.0	x 10 ⁻⁴	$V_{CE} = 10V, I_{C} = 1.0mA,$	
Small Signal Current Gain	h _{fe}	100	400	_	f = 1.0kHz	
Output Admittance	h _{oe}	1.0	40	μS	1	
Current Gain-Bandwidth Product	f⊤	300	_	MHz	$V_{CE} = 20V, I_{C} = 10mA,$ f = 100MHz	
SWITCHING CHARACTERISTICS						
Delay Time	t _d	_	35	ns	$V_{CC} = 3.0V, I_C = 10mA,$	
Rise Time	t _r	_	35	ns	$V_{BE(off)} = -0.5V, I_{B1} = 1.0mA$	
Storage Time	ts	_	200	ns	$V_{CC} = 3.0V, I_{C} = 10mA,$	
Fall Time	t _f		50	ns	$I_{B1} = I_{B2} = 1.0 \text{mA}$	

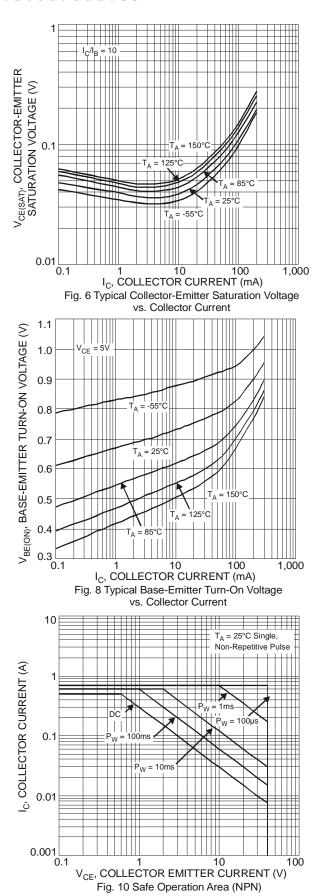
Notes: 4. Measured under pulsed conditions. Pulse width = 300μ s. Duty cycle $\leq 2\%$

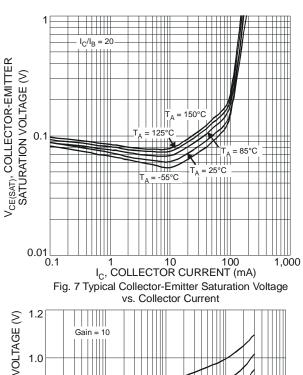


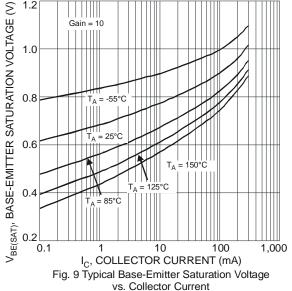








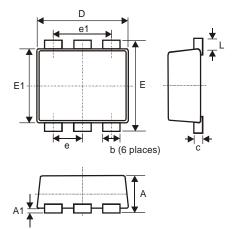






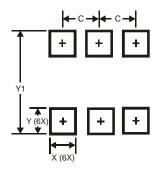


Package Outline Dimensions



SOT-963				
Dim	Min	Max	Тур	
Α	0.40	0.50	0.45	
A1	0	0.05	-	
С	0.120	0.180	0.150	
D	0.95	1.05	1.00	
Е	0.95	1.05	1.00	
E1	0.75	0.85	0.80	
L	0.05	0.15	0.10	
b	0.10	0.20	0.15	
е	9 0.35 Typ			
e1	0.70 Typ			
All	All Dimensions in mm			

Suggest Pad Layout



Dimensions	Value (in mm)
С	0.350
Х	0.200
Υ	0.200
Y1	1 100





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